

MA2S304

Silicon epitaxial planar type

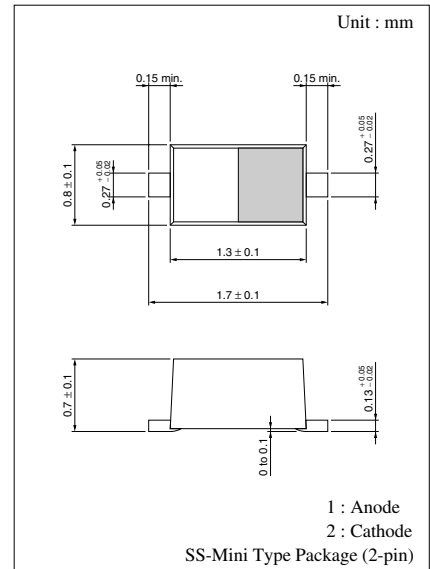
For VCO

■ Features

- Good linearity and large capacitance-ratio in C_D — V_R relation
- Small series resistance r_D
- SS-mini type package, allowing downsizing of equipment and automatic insertion through the taping package

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	30	V
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Marking Symbol: K

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 28\text{ V}$			10	nA
Diode capacitance	$C_{D(1V)}$	$V_R = 1\text{ V}, f = 1\text{ MHz}$	24.8		29.8	pF
	$C_{D(4V)}$	$V_R = 4\text{ V}, f = 1\text{ MHz}$	6.0		8.3	pF
Capacitance ratio	$C_{D(1V)}/C_{D(4V)}$		3.0			—
Series resistance*	r_D	$V_R = 4\text{ V}, f = 100\text{ MHz}$			1.0	Ω

Note) 1. Rated input/output frequency: 100 MHz

2. *: r_f measuring instrument: YHP MODEL 4191A RF IMPEDANCE ANALYZER

